SHEET <u>1</u> of <u>3</u>

INFORMATION DISCLOSURE **CITATION** 

PTO-1449

Atty. Docket No. NTI-004

Serial No.

09/814,025

**Applicant** 

KARKLIN, Linard

**Filing Date** 

Group

3/20/2001

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	S.A	6,081,659	6/27/2000·	Garza, et al.	395	500.22	4/26/1999
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